



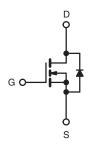
N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}(m\Omega)(Typ.)$	I _D (A) ^a	Q _g (Typ.)				
150	8.1 at V _{GS} = 10 V	99	36 nC				

- **FEATURES**
 - DT-SGT Power MOSFET
 - · Very Low On-resistance
- Excellent FOM(Figure of Merit)
- 100% ΔVDS & UIS & Rg Tested

APPLICATIONS

- DC-DC Converter
- · Hard Switching and High Speed Circuit
- Synchronous Rectification in SMPS



N-Channel MOSFET

TO-220 Pin Configuration Top View



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)								
PARAMETER	SYMBOL	LIMIT	UNIT					
Drain-Source Voltage	V _{DS}	150	V					
Gate-Source Voltage	V_{GS}	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \					
Continuous Proin Current /T = 175 °C\2	T _C = 25 °C	1	99					
Continuous Drain Current (T _J = 175 °C) ^a	T _C = 100 °C	- I _D	70	Α				
Pulsed Drain Current ^b	I _{DM}	309						
Single Avalanche Energy	E _{AS}	672	mJ					
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	254	W				
waximum rowei bissipation	T _C = 100 °C	T PD	127] vv				
Operating Junction and Storage Temperature R	T _J , T _{stg}	-55 to +175	°C					

THERMAL RESISTANCE RATINGS						
PARAMETER SYMBOL LIMIT UN						
Junction-to-Ambient (PCB Mount) ^d	R_{thJA}	35	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.59	C/VV			

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	V _{GS} = 0 V, I _D = 250 μA	150	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	-	4.0	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zoro Coto Voltogo Droin Current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V	-	-	1	μΑ
Zero Gate Voltage Drain Current		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	99	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A	-	8.1	9.3	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 5 V, I _D = 20 A	-	43	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	2330	-	pF
Output Capacitance	Coss	V _{GS} = 0 V, V _{DS} = 75 V, f = 1 MHz	-	316	-	
Reverse Transfer Capacitance	C _{rss}		-	17	-	
Total Gate Charge c	Qg		-	36	-	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	10	-	
Gate-Drain Charge ^c	Q_{gd}		-	7.7	-	
Gate Resistance	R _g	f = 1 MHz	-	2.2	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	8.6	-	ns
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, \text{ R}_{GEN} = 3 \Omega, \text{ I}_{D} = 20 \text{ A},$	-	17	-	
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	28	-	
Fall Time ^c	t _f		-	22	-	
Drain-Source Body Diode Ratings and	Characterist	tics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	99	А
Pulsed Current	I _{SM}		-	-	309	Α
Forward Voltage ^a	V_{SD}	I _F = 2 A, V _{GS} = 0 V	-	0.7	1.2	V
Reverse Recovery Time	t _{rr}	1 00 A di/dt = 400 A/cc	-	76	-	ns
Reverse Recovery Charge	Q_{rr}	$I_F = 20 \text{ A, di/dt} = 100 \text{ A/µs}$		227	-	nC

Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25°C unless otherwise noted)

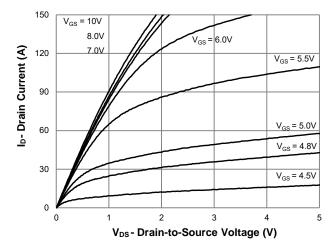


Figure 1: Output Characteristics

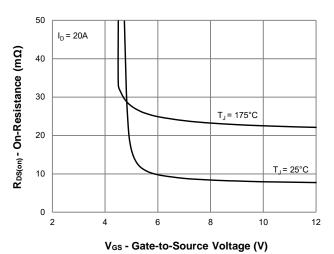


Figure 3: On-Resistance vs. Gate-Source Voltage

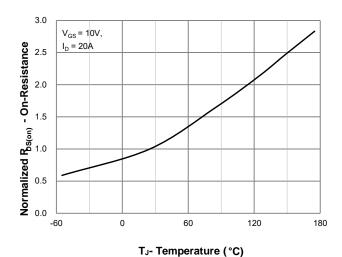


Figure 5: On-Resistance vs. Junction Temperature

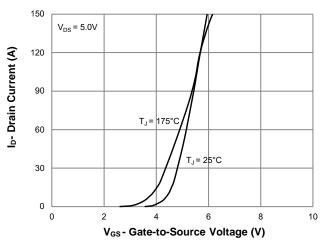


Figure 2: Transfer Characteristics

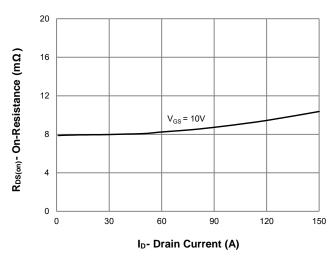
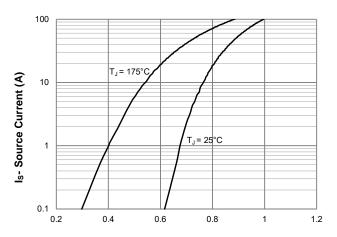


Figure 4: On-Resistance vs. Gate-Source Voltage



V_{SD} - Source-to-Drain Voltage (V)

Figure 6: Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTICS (25°C unless otherwise noted)

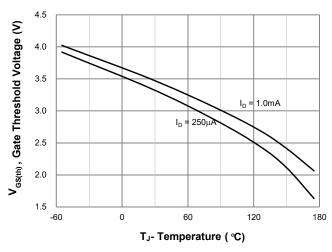


Figure 7: Gate Threshold Variation vs. Junction Temperature

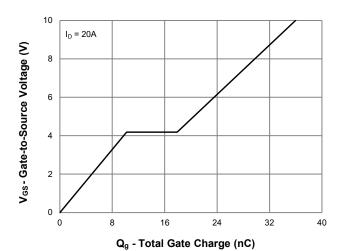
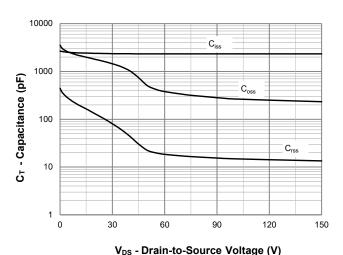
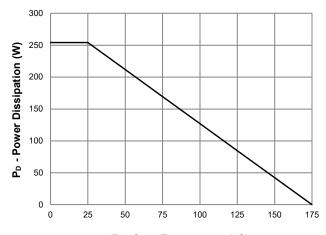


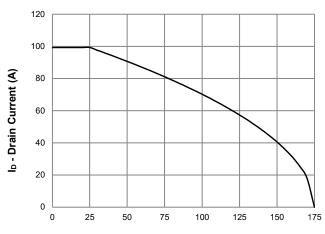
Figure 8: Gate Charge Characteristics



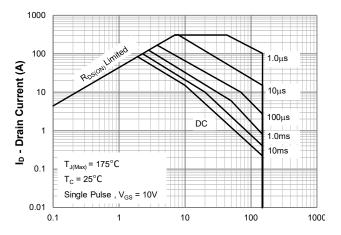


T_C - Case Temperature (°C) Figure 10: Power Derating





T_C - Case Temperature (°C) Figure 11: Current Derating



V_{DS} - Drain-to-Source Voltage (V)

Figure 12: Safe Operating Area



TYPICAL CHARACTERISTICS (25°C unless otherwise noted)

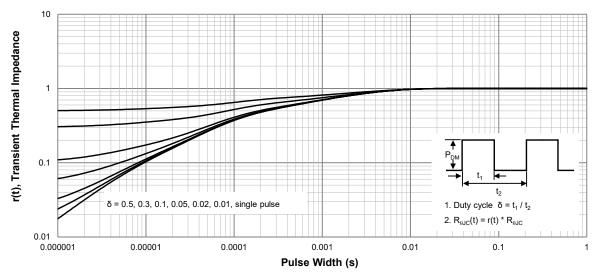
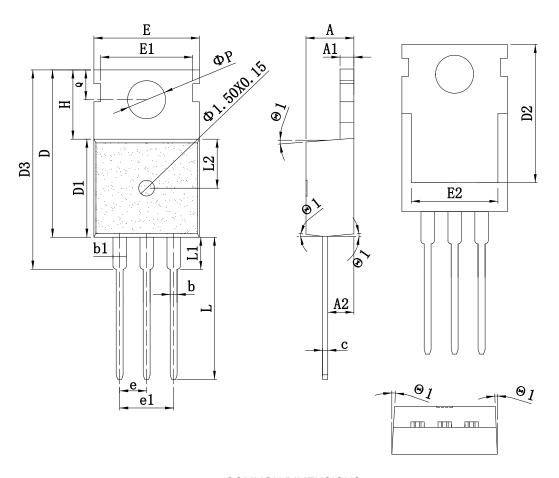


Figure 13: Normalized Maximum Transient Thermal Impedance



TO-220_3L-A PACKAGE OUTLINE

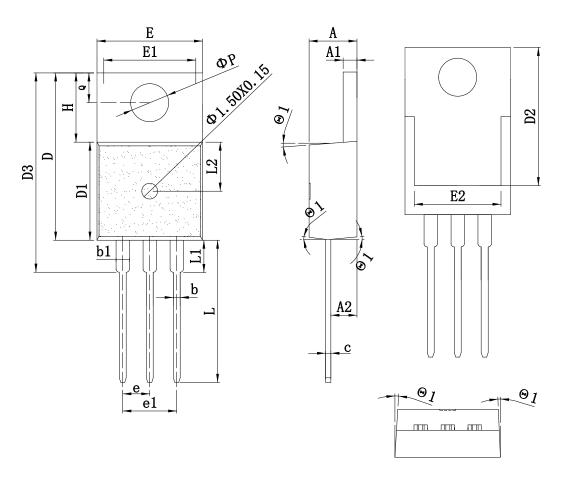


COMMON DIMENSIONS (UNITS OF MEASURE= MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX	STIVIBUL	MIN	TYP	MAX
Α	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	е	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
С	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	1	1	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φР	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°



TO-220_3L-B PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE= MILLIMETER)

SYMBOL	mm			SYMBOL	mm		
	MIN	TYP	MAX	STIVIBUL	MIN	TYP	MAX
Α	4.15	4.50	4.80	E1	8.25	8.70	9.15
A1	1.15	1.30	1.50	E2	7.20	8.00	8.80
A2	2.10	2.40	2.65	е	2.38	2.54	2.74
b	0.65	0.80	1.00	e1	5.08REF		
b1	1.10	1.33	1.80	Н	6.20	6.50	6.90
С	0.35	0.50	0.65	L	12.75	13.28	13.70
D	14.25	15.75	16.15	L1	-	-	3.50
D1	8.70	9.20	9.60	L2	2.30	4.65	7.00
D2	12.30	13.10	13.85	φР	3.40	3.65	3.85
D3	16.20	18.80	20.60	Q	2.50	2.80	3.00
Е	8.68	10.02	11.00	θ	2°	-	7°





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